

Supplemental Materials: Surface passivated and encapsulated ZnO atomic layer by high- κ ultrathin MgO layer

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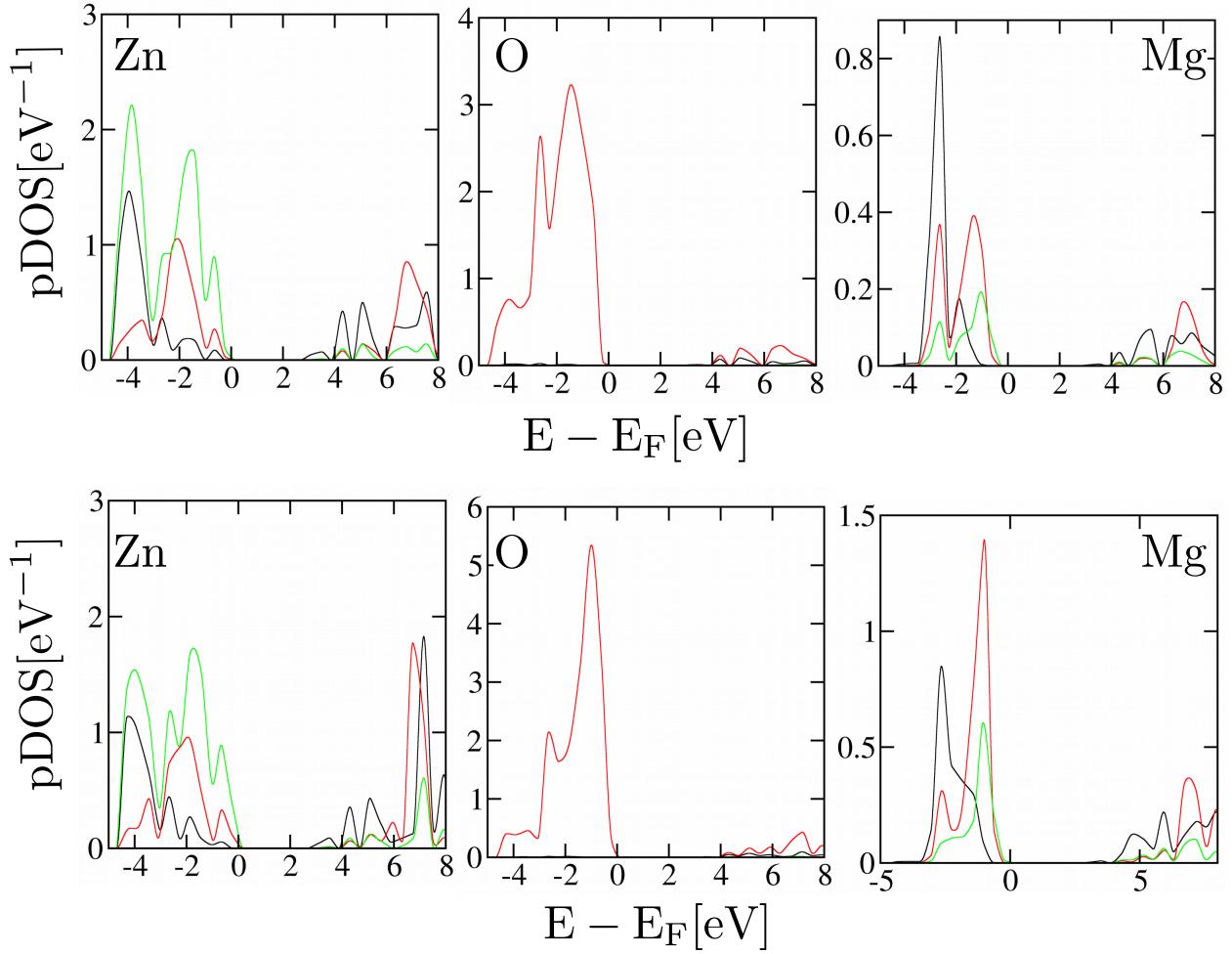


Figure 1: **Electronic structure of vdW heterostructures.** Partial density of states of Zn, O, and Mg. Note, the O atoms from ZnO and MgO have been plotted together. However, over 98% of the contributions of O to the vdW materials are from ZnO. The top panel is for MgO/ZnO while the bottom panel is for MgO/ZnO/MgO. Black, red, and green lines in the plots correspond to *s*, *p*, and *d* orbitals, respectively.

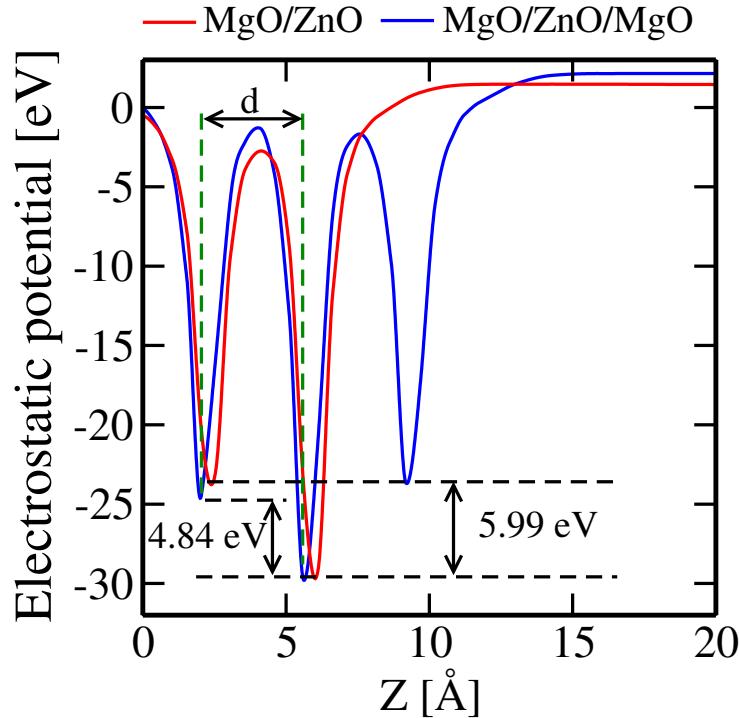


Figure 2: Electronic band levels of ZnO-based vdW heterostructures. Electrostatic potential profile along the z -direction of the crystallographic plane. For MgO/ZnO vdW heterostructure, the charge transfer across the heterojunction needs to overcome an energy barrier of 5.90 ± 0.02 eV, and a transfer distance of 3.72 ± 0.02 Å. For MgO/ZnO/MgO, the charge transfer across the heterointerface needs to overcome an energy barrier of 4.84 ± 0.02 (5.99 ± 0.02 eV) and a transfer distance of 3.59 ± 0.02 (3.72 ± 0.02 Å) for the top (bottom) interfaces. d is a typical transfer distance.

Below we present the crystal information in the primitive cell; the Crystallographic Information File format is used.

MgO passivated ZnO - MgO/ZnO crystal structure

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MgO encapsulated ZnO - MgO/ZnO/MgO crystal structure

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Zn4	1.0	0.500000	0.500000	0.229047	Biso	1.000000	Zn

Acknowledgment

This work was supported by the Lehigh University Start-up fund to CEE and the U.S. Army Research Laboratory. Supercomputer support is provided by the DOD High-Performance Computing Modernization Program at the Army Engineer Research and Development Center, Vicksburg, MS.